

# SINTERED GLASS JUNCTION AVALANCHE RECTIFIER

2.0.156(4.0) min.

0.156(4.0) min.

0.140(3.6) min.

0.032(0.82) max.

Dimensions in inches and (millimeters)

Reverse Voltage - 1000 V Forward Current - 2.0 A

## **FEATURE**

Glass passivated
High maximum operating temperature
Low leakage current
Excellent stability
Guaranteed avalanche energy absorption capability

#### **MECHANICAL DATA**

Case: SOD-57 sintered glass case

Terminal: Plated axial leads solderable per

MIL-STD 202E, method 208C

Polarity: color band denotes cathode end

Mounting position: any

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

	SYMBOL	BYW56	units
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	1000	V
Maximum RMS Voltage	V <sub>RMS</sub>	700	V
Maximum DC blocking Voltage	$V_{DC}$	1000	V
Maximum Average Forward Rectified  Current 3/8"lead length at Ttp=45°C	I <sub>FAV</sub>	2.0	А
Peak Forward Surge Current at Tp=10ms half sinewave	I <sub>FSM</sub>	50	Α
Maximum Forward Voltage at Forward Current 1A	V <sub>F</sub>	1.00	V
Non-repetitive peak reverse avalanche energy at I <sub>(BR)R</sub> =1A	E <sub>R</sub>	20	mJ
Maximum DC Reverse Current $Ta = 25$ °C at rated DC blocking voltage $Ta = 100$ °C	I <sub>R</sub>	1.0 10.0	μΑ
Typical Reverse Recovery Time (Note 1)	Trr	3.0	μS
Typical Thermal Resistance (Note 2)	R <sub>th(ja)</sub>	46	KW
Storage and Operating Junction Temperature	Tstg, Tj	-65 to +175	°C

#### Note:

- 1. Reverse Recovery Condition If =0.5A, Ir =1.0A, Irr =0.25A
- 2. I =10mm, $T_L$  = constant



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#### **RATINGS AND CHARACTERISTIC CURVES**

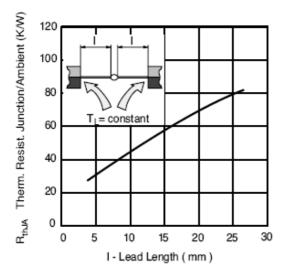


Figure 1. Typ. Thermal Resistance vs. Lead Length

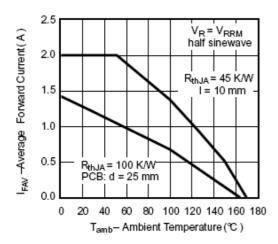


Figure 3. Max. Average Forward Current vs. Ambient Temperature

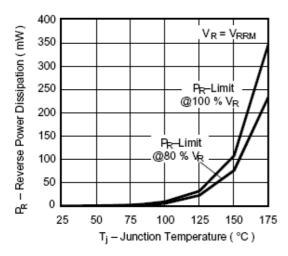


Figure 5. Max. Reverse Power Dissipation vs. Junction Temperature

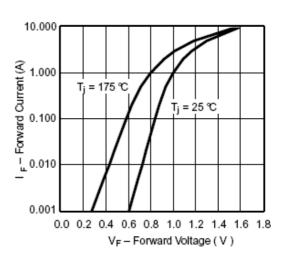


Figure 2. Forward Current vs. Forward Voltage

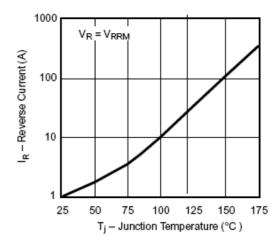


Figure 4. Reverse Current vs. Junction Temperature

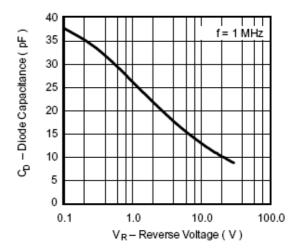


Figure 6. Diode Capacitance vs. Reverse Voltage